

## IRF634B\_FP001 Information

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For Reference Only

Part Number IRF634B\_FP001

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products<br/>Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 250V 8.1A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# IRF634B\_FP001 Specifications

Manufacturer Part Number         IRF634B_FP001           Manufacturer         Fairchild/ON Semiconductor           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         250V           Current - Continuous Drain (Id) @ 25°C         8.1A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         38nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1000pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         74W (Tc)           Rds On (Max) @ Id, Vgs         450 mOhm @ 4.05A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3		
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Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

## IRF634B\_FP001 Guarantees



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## IRF634B\_FP001 Payment Methods





















## IRF634B\_FP001 Shipping Methods













If you have any question about IRF634B\_FP001, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com